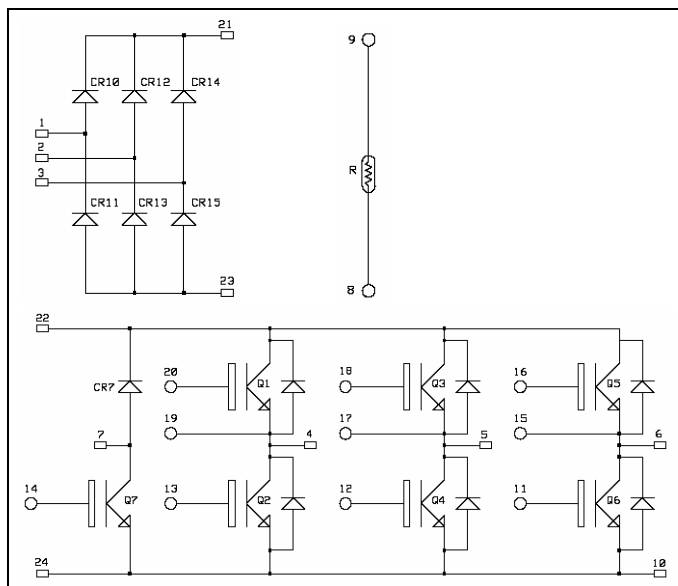
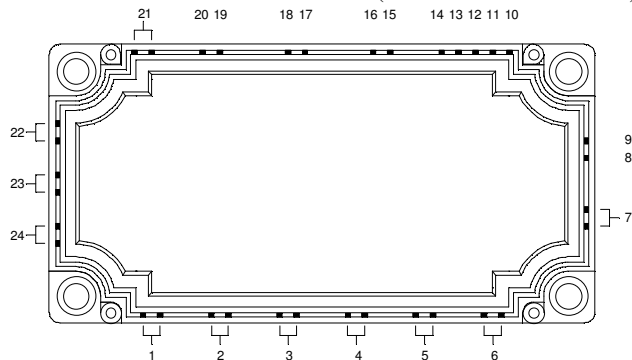


Input rectifier bridge + Brake + 3 Phase Bridge Trench IGBT® Power Module

$V_{CES} = 1200V$
 $I_C = 50A @ T_c = 80^\circ C$



APTGT50X120RTP3: Without Brake (Pin 7 & 14 not connected)



Application

- AC Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

1. Absolute maximum ratings

Diode rectifier Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		1600	V
I_D	DC Forward Current	$T_C = 80^\circ C$	80	A
I_{FSM}	Surge Forward Current	$T_j = 25^\circ C$	500	
		$T_j = 150^\circ C$	400	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

IGBT & Diode Brake (only for APTGT50X120BTP3) Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ\text{C}$ 55	A
		$T_C = 80^\circ\text{C}$ 35	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ\text{C}$ 80	
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 200	W
I_F	DC Forward Current	$T_C = 80^\circ\text{C}$ 15	A

IGBT & Diode Inverter Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ\text{C}$ 75	A
		$T_C = 80^\circ\text{C}$ 50	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ\text{C}$ 100	
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 270	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ\text{C}$ 100A @ 1100V	
I_F	DC Forward Current	$T_C = 80^\circ\text{C}$ 50	A
I_{FRM}	Repetitive Peak Forward Current	$t_p = 1\text{ms}$ 100	

2. Electrical Characteristics

Diodes Rectifier Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_R	Reverse Current	$V_R = 1600\text{V}$ $T_j = 150^\circ\text{C}$		3		mA
V_F	Forward Voltage	$I_F = 50\text{A}$ $T_j = 150^\circ\text{C}$		1.0		V
R_{thJC}	Junction to Case				0.65	$^\circ\text{C/W}$

IGBT Brake & Diode (only for APTGT50X120BTP3) Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$, $V_{CE} = 1200\text{V}$		4		mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$ $T_j = 25^\circ\text{C}$ $I_C = 35\text{A}$		1.8	2.2	V
		$T_j = 125^\circ\text{C}$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$			500	nA
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$, $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		2530		pF
C_{oes}	Output Capacitance			132		
C_{res}	Reverse Transfer Capacitance			115		
V_F	Forward Voltage	$V_{GE} = 0\text{V}$ $T_j = 25^\circ\text{C}$ $I_F = 35\text{A}$		2.3	2.7	V
		$T_j = 125^\circ\text{C}$		2.5		
R_{thJC}	Junction to Case	IGBT			0.6	$^\circ\text{C/W}$
		Diode			1.5	

IGBT & Diode Inverter Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV _{CES}	Collector - Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 3mA	1200			V
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1200V			5	mA
V _{CE(on)}	Collector Emitter on Voltage	V _{GE} = 15V I _C = 50A	T _j = 25°C T _j = 125°C	1.4 2.0	2.1	V
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 2 mA	5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			500	nA
C _{ies}	Input Capacitance	V _{GE} = 0V		3600		pF
C _{oss}	Output Capacitance	V _{CE} = 25V		188		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		163		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 50A R _G = 18Ω		85		ns
T _r	Rise Time			30		
T _{d(off)}	Turn-off Delay Time			420		
T _f	Fall Time			65		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 50A R _G = 18Ω		90		ns
T _r	Rise Time			45		
T _{d(off)}	Turn-off Delay Time			520		
T _f	Fall Time			90		
E _{off}	Turn off Energy			5.8		
V _F	Forward Voltage	V _{GE} = 0V I _F = 50A	T _j = 25°C T _j = 125°C	1.6 1.6	2.2	V
Q _{rr}	Reverse Recovery Charge	I _F = 50A V _R = 600V di/dt=990A/μs	T _j = 25°C T _j = 125°C	5.2 9.4		μC
R _{thJC}	Junction to Case		IGBT Diode		0.45 0.75	°C/W

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		5		kΩ
B _{25/50}	T ₂₅ = 298.16 K		3375		K

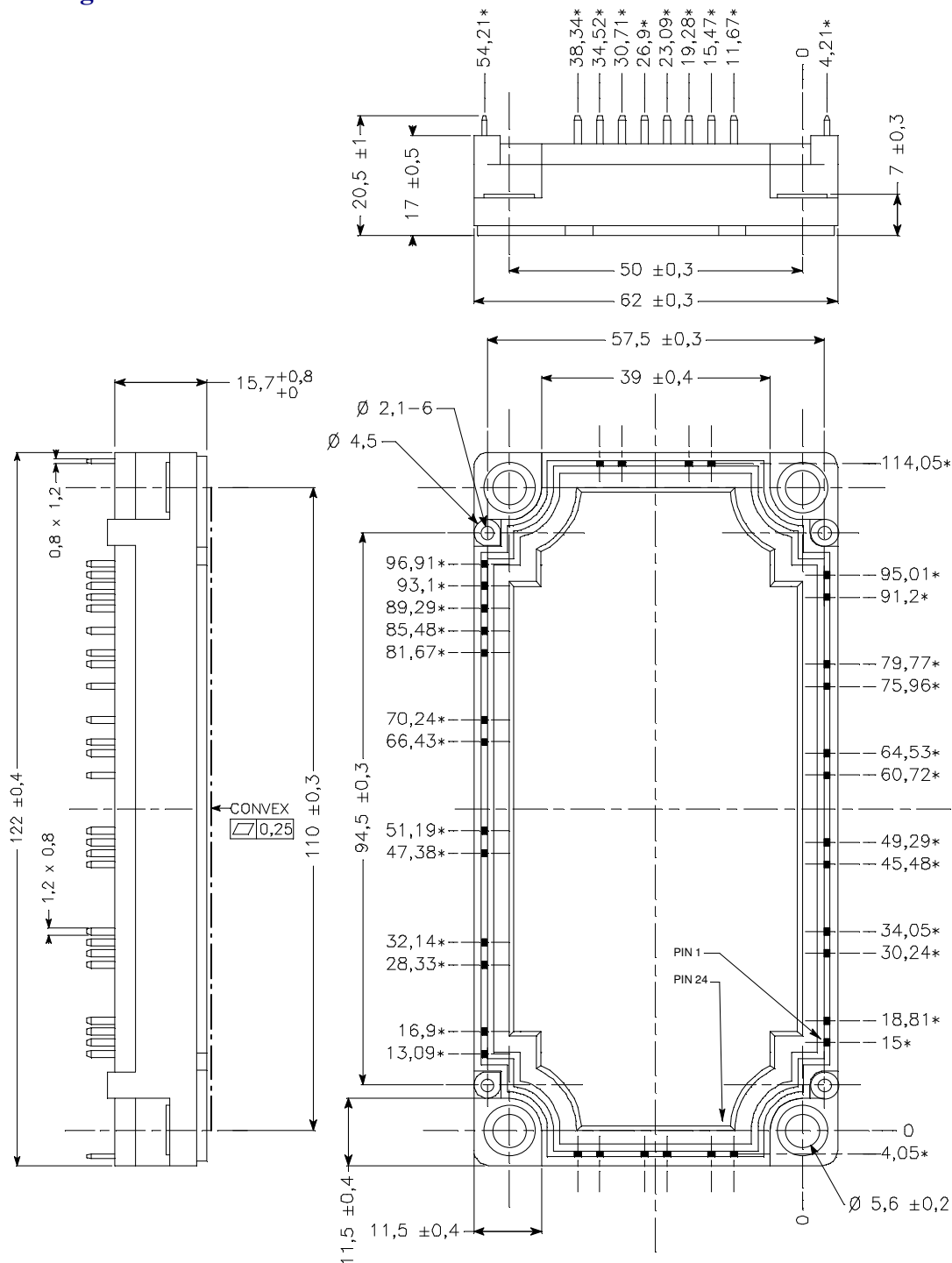
$$R_T = \frac{R_{25}}{\exp \left[B_{25/50} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

3. Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		125	
Torque	Mounting torque	To Heatsink	M5	3.3	N.m
Wt	Package Weight			300	g

4. Package outline



ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : $\pm 0,4$

APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.